

Description

The HSK0008 is the high cell density trenched N-ch MOSFETs, which provides excellent R_{DS(ON)} and efficiency for most of the small power switching and load switch applications.

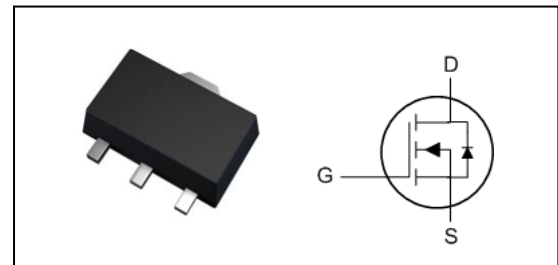
The HSK0008 meet the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent C_{dv/dt} effect decline
- Advanced high cell density Trench technology

Product Summary

V _{DS}	100	V
R _{DS(ON),max}	310	mΩ
I _D	2.2	A

SOT89 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	100	V
V _{GS}	Gate-Source Voltage	±20	V
I _D @T _A =25°C	Continuous Drain Current, V _{GS} @ 10V ₁	2.2	A
I _D @T _A =70°C	Continuous Drain Current, V _{GS} @ 10V ₁	1.7	A
I _{DM}	Pulsed Drain Current ₂	5.8	A
P _D @T _A =25°C	Total Power Dissipation ₃	1.5	W
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-ambient ₁	---	85	°C/W
R _{θJC}	Thermal Resistance Junction-Case ₁	---	36	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
B _V DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	100	---	---	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =2A	---	260	310	mΩ
		V _{GS} =4.5V, I _D =1A	---	270	320	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	1.5	2.5	V
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =80V, V _{GS} =0V, T _J =25°C	---	---	5	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =2A	---	5.4	---	S
Q _g	Total Gate Charge (10V)	V _{DS} =80V, V _{GS} =10V, I _D =1A	---	9.7	---	nC
Q _{gs}	Gate-Source Charge		---	1.6	---	
Q _{gd}	Gate-Drain Charge		---	1.7	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =50V, V _{GS} =10V, R _G =3.3Ω I _D =1A	---	1.6	---	ns
T _r	Rise Time		---	19	---	
T _{d(off)}	Turn-Off Delay Time		---	13.6	---	
T _f	Fall Time		---	19	---	
C _{iss}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	---	508	---	pF
C _{oss}	Output Capacitance		---	29	---	
C _{rss}	Reverse Transfer Capacitance		---	16.4	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,4}	V _G =V _D =0V, Force Current	---	---	2.2	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V, I _S =1A, T _J =25°C	---	---	1.2	V
T _{rr}	Reverse Recovery Time	I _F =2A, dI/dt=100A/us, T _J =25°C	---	17	---	nS
Q _{rr}	Reverse Recovery Charge		---	14	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I_D and I_{DM}, in real applications, should be limited by total power dissipation.



Typical Characteristics

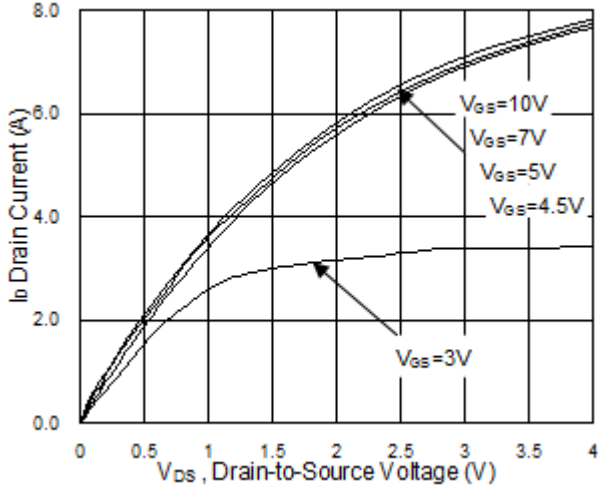


Fig.1 Typical Output Characteristics

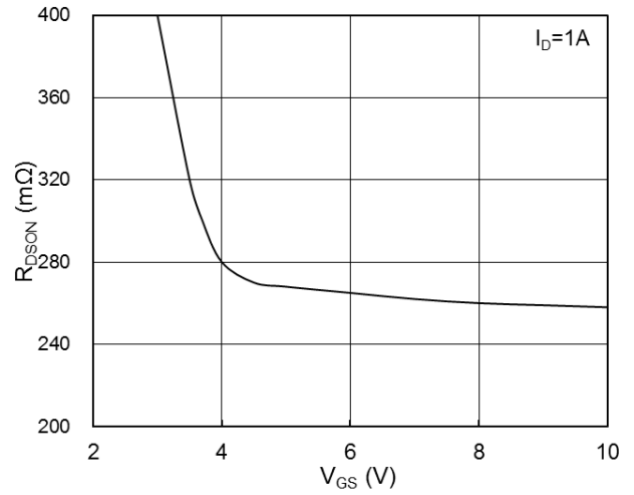


Fig.2 On-Resistance vs. G-S Voltage

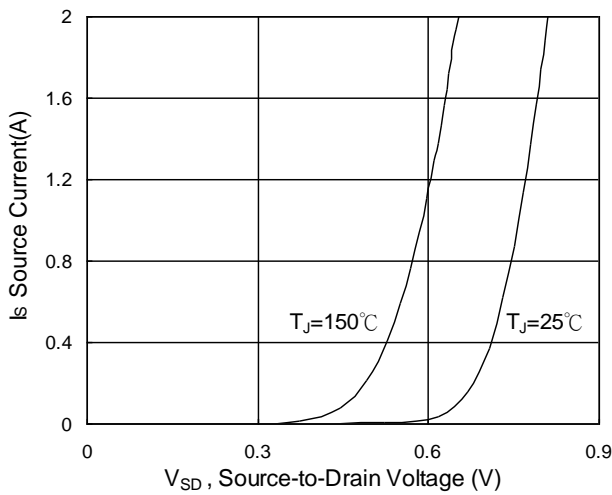


Fig.3 Source Drain Forward Characteristics

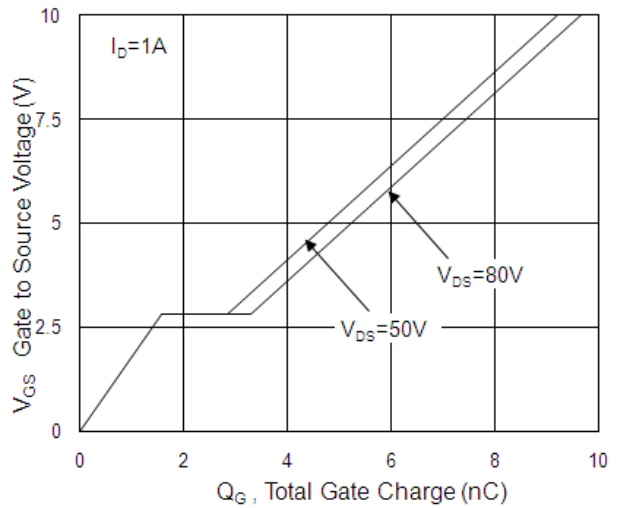


Fig.4 Gate-Charge Characteristics

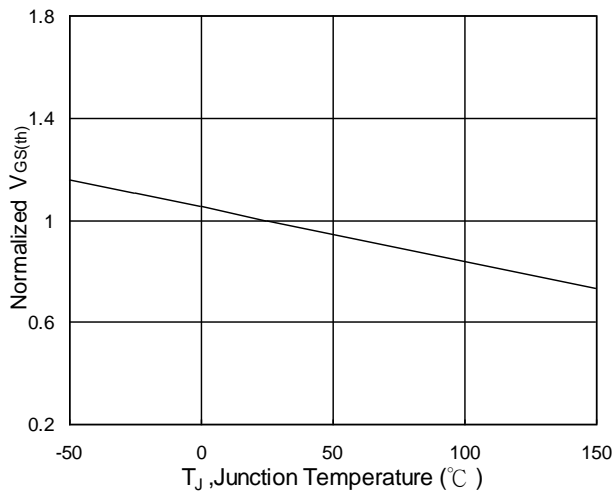


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

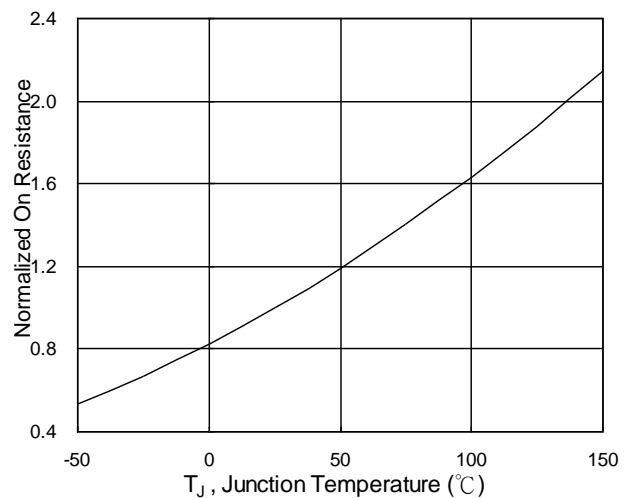


Fig.6 Normalized $R_{DS(on)}$ vs. T_J



N-Ch 100V Fast Switching MOSFETs

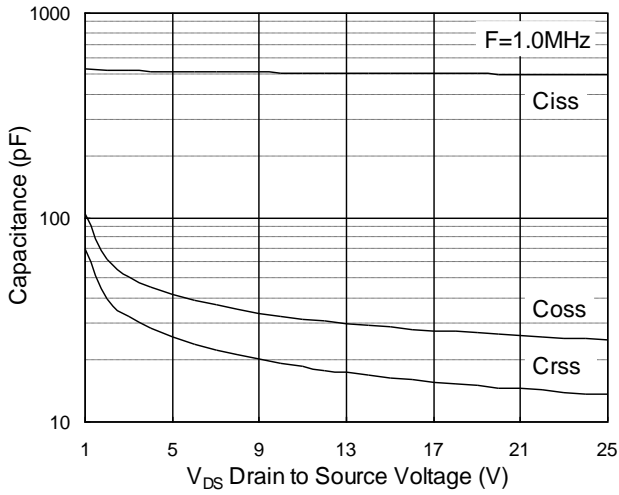


Fig.7 Capacitance

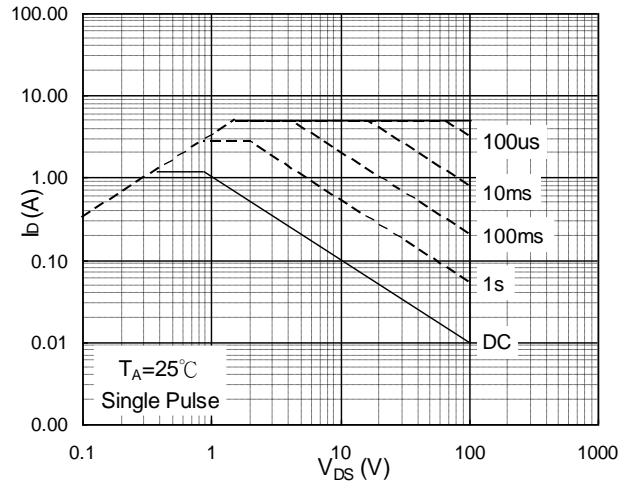


Fig.8 Safe Operating Area

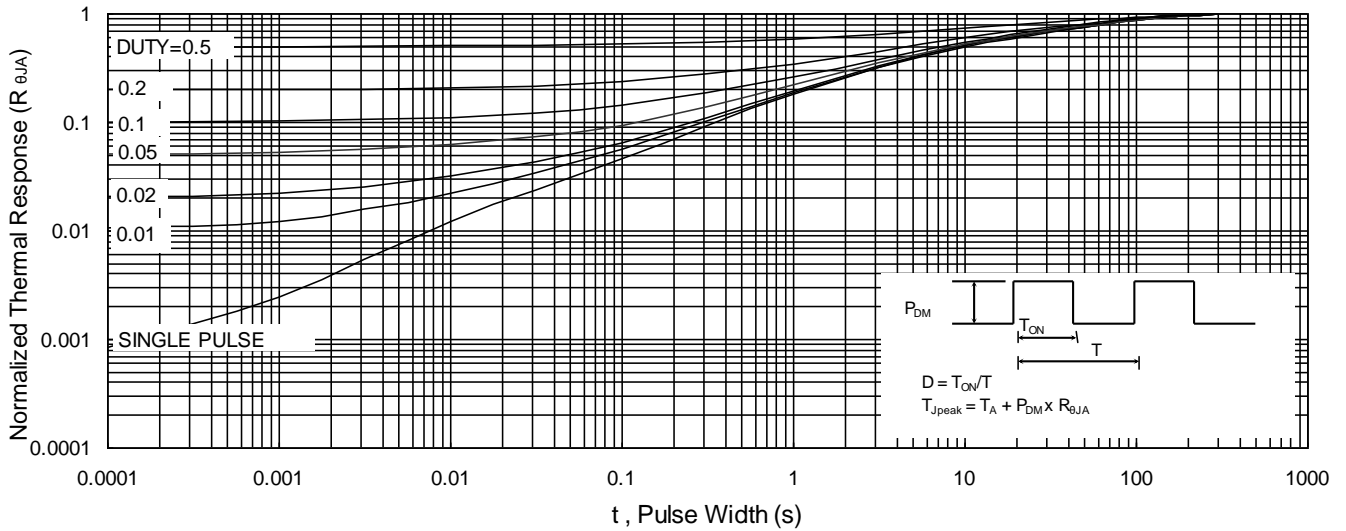


Fig.9 Normalized Maximum Transient Thermal Impedance

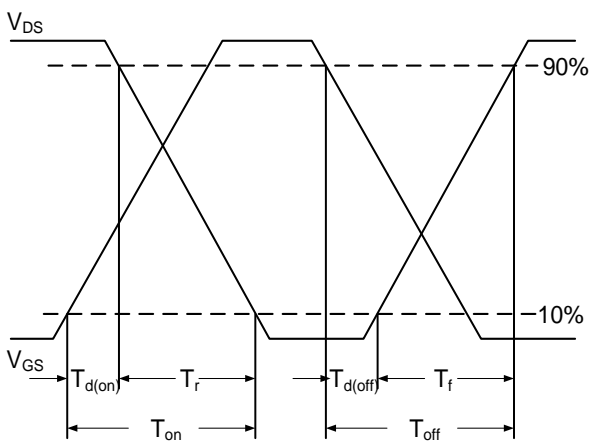


Fig.10 Switching Time Waveform

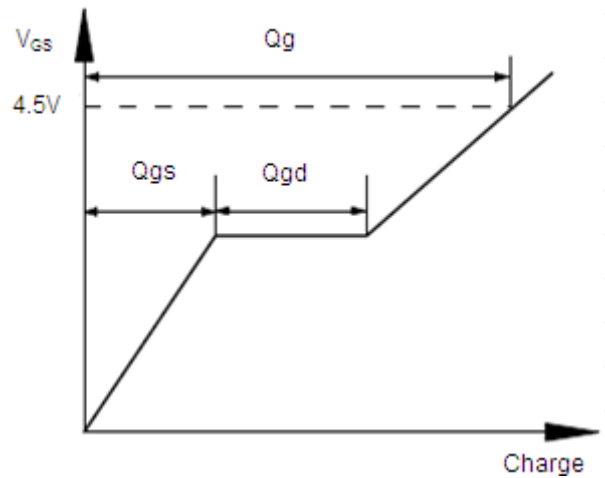
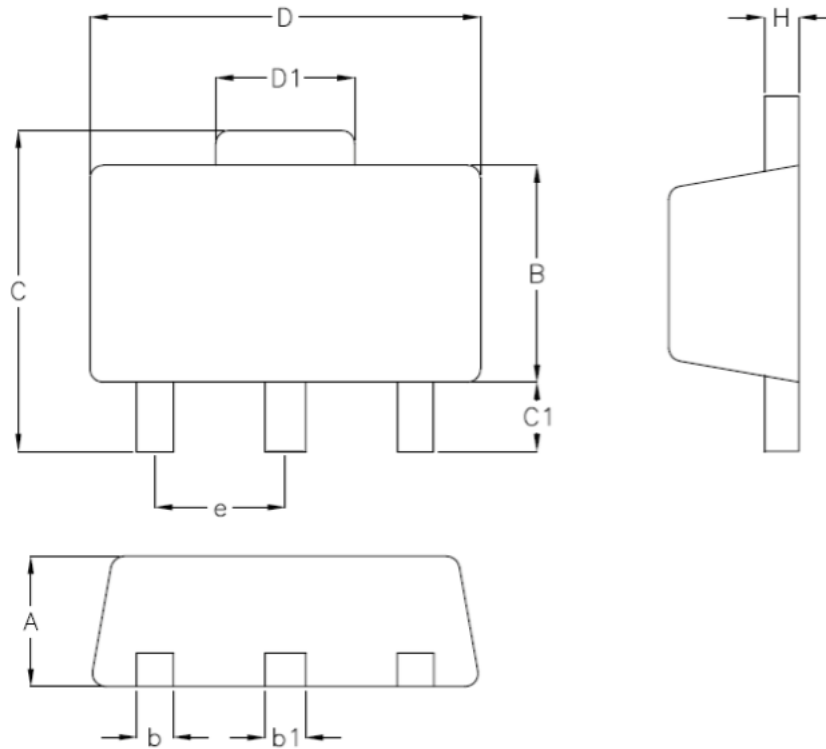


Fig.11 Gate Charge Waveform



Ordering Information

Part Number	Package code	Packaging
HSK0008	SOT-89	4000/Tape&Reel



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.397	1.600	0.055	0.063
b	0.420	0.540	0.017	0.021
b1	0.420	0.540	0.017	0.021
B	2.388	2.591	0.094	0.102
C	3.937	4.242	0.155	0.167
C1	0.787	1.194	0.031	0.047
D	4.394	4.597	0.173	0.181
D1	1.397	1.753	0.055	0.069
e	1.448	1.549	0.057	0.061
H	0.350	0.44	0.014	0.017